## Unijunction Transistor



### RoHS Compliant



A PN unijunction transistor in a TO–92 type package designed for use in pulse and timing circuits, sensing circuits and thyristor trigger circuits



### **Absolute maximum Ratings:**

(TA = +25°C unless otherwise specified)

Power Dissipation, PD : 300mW

Derate Above 25°C : 3.0mW/°C

RMS Emitter Current, IE(RMS) : 50mA

Peak Pulse Emitter Current (Note 1) Current, iE : 1.5A

Emitter Reverse Voltage, VB2E : 30V

Interbase Voltage, VB2B1 : 35V

Operating Junction Temperature Range, T<sub>J</sub> : -65°C to +125°C Storage Temperature Range, Tstg : -65°C to +150°C

### Electrical Characteristics: (TA = +25°C Unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Instrinsic Standoff Ratio		V <sub>B2B1</sub> = 10V, Note3	0.70	-	0.85	-
Interbase Resistance	rвв		4.0	6.0	9.1	kΩ
Interbase Resistance Temperature Coefficient			0.1	-	0.9	%/°C
Emitter Saturation Voltage	VEB1(sat)	V <sub>B2B1</sub> = 10V, I <sub>E</sub> = 50mA, Note 4	-	2.5	-	V
Modulated interbase Current	B2(mod)	V <sub>B2B1</sub> = 10V, I <sub>E</sub> = 50mA	-	15	-	mA
Emitter Reverse Current	IEB20	V <sub>B2E</sub> = 30V, I <sub>B1</sub> = 0	-	0.005	1	μA
Peak Point Emitter Current	lР	V <sub>B2B1</sub> = 25V	-	1	5	μA
Valley Point Current	lv	V <sub>B2B1</sub> = 20V, R <sub>B2</sub> = 100Ω, Note 4	4	7	-	mA
Base-One Peak Pulse Voltage	V <sub>OB1</sub>		5	8	-	V

#### Notes:

- 1. Duty Cycle ≤ 1% PRR = 10PPS.
- 2. Based upon power dissipation at TA = +25°C
- 3. Intrinsic standoff ratio is essentially constant with temperature and interbase voltage and is defined by the equation:

VP - VBB + VD

Where: VP = Peak Point Emitter Voltage; VBB = interbase Voltage;

V<sub>D</sub> = Junction Diode Drop (~0.5V).

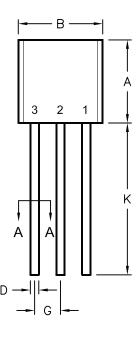
4. Use Pulse techniques: Pulse width ~ 300μS, Duty Cycle ≤ 2% to avoid internal heating due to interbase modulation which may result in erroneous readings.





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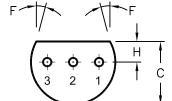




**PNP** 

Dim	Min	Max	
Α	4.32	5.33	
В	4.45	5.2	
С	3.18	4.19	
D	0.41	0.55	
Е	0.35	0.5	
F	5°		
G	1.14	1.4	

B2



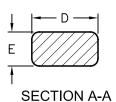
Dimensions : Millimetres

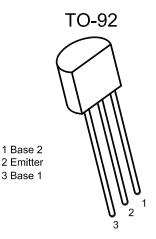
1.14

12.7

1.53

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#### **Part Number Table**

Description	Part Number		
Unijunction Transistor, TO-92, PN	2N4871		

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